

N-channel 100 V 5 m Ω standard level MOSFET in I2PAK

Rev. 3 — 26 September 2011

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a I2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1.	Quick reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	<u>[1]</u>	-	-	120	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	338	W
Тj	junction temperature			-55	-	175	°C
Static cha	aracteristics						
R _{DSon}	drain-source on-state resistance	$\label{eq:GS} \begin{array}{l} V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \\ T_{j} = 100 \text{ °C}; \text{ see } \underline{\text{Figure 12}}; \\ \text{see } \underline{\text{Figure 13}} \end{array}$		-	7.7	9	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 13</u>	[2]	-	4.3	5	mΩ
Dynamic	characteristics						
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 75 A;		-	49	-	nC
Q _{G(tot)}	total gate charge	$V_{DS} = 50 \text{ V}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 15}$		-	170	-	nC
Avalanch	e ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy			-	-	537	mJ

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- [1] Continuous current limited by package.
- [2] Measured 3 mm from package.

2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

SOT226 (I2PAK)

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN5R0-100ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

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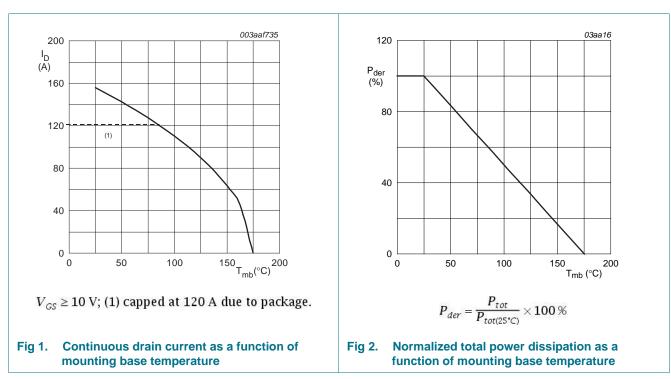
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

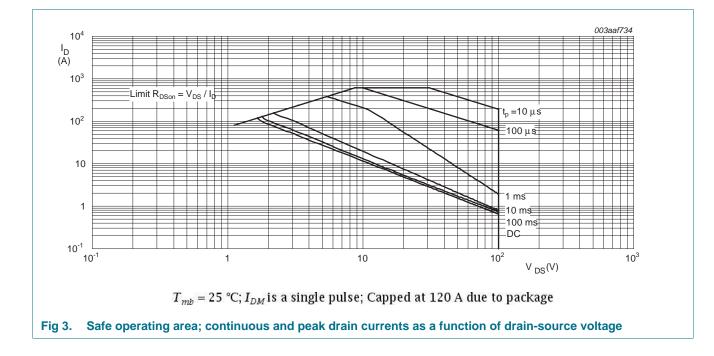
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Symbol	Parameter	Conditions		Min	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	100	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ		-	100	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V}; \text{ T}_{j} = 100 \text{ °C}; \text{ see } \frac{\text{Figure 1}}{100 \text{ Figure 1}}$		-	110	А
		V_{GS} = 10 V; T_{mb} = 25 °C; see <u>Figure 1</u>	[1]	-	120	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3		-	622	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	338	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-dr	ain diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	622	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 120 A; V_{sup} ≤ 100 V; R_{GS} = 50 Ω; Unclamped		-	537	mJ

[1] Continuous current limited by package



PSMN5R0-100ES

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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.44	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Vertical in free air	-	60	-	K/W

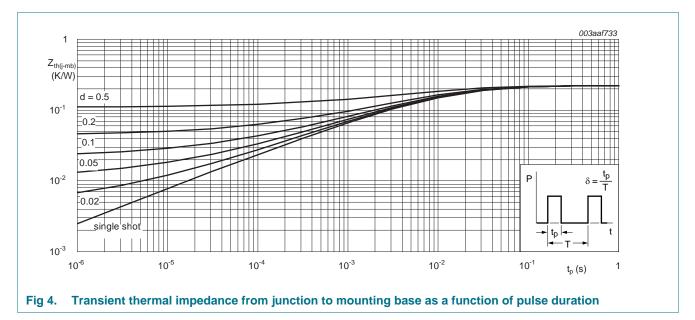


Table 5. Thermal characteristics

N-channel 100 V 5 mΩ standard level MOSFET in I2PAK

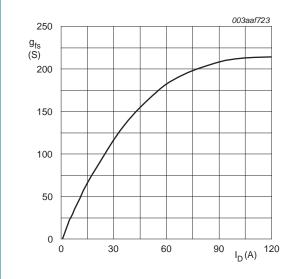
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	100	-	-	V
	voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	90	-	-	V
V _{GS(th)} gate-source	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see Figure 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 10</u>	2	3	4	V
I _{DSS}	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.08	10	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	10	100	nA
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 $^{\circ}C$	-	10	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; see <u>Figure 12;</u> see <u>Figure 13</u>	-	12	14	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 100 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	7.7	9	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ I see Figure 13	<u>1]</u> -	4.3	5	mΩ
R _G	gate resistance	f = 1 MHz	-	0.9	-	Ω
Dynamic	characteristics					
Q _{G(tot)}	Q _{G(tot)} total gate charge	$I_D = 75 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	170	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	140	-	nC
Q _{GS}	gate-source charge	$I_D = 75 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$	-	48	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	31	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	17.3	-	nC
Q _{GD}	gate-drain charge		-	49	-	nC
V _{GS(pl)}	gate-source plateau voltage	V _{DS} = 50 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	5.1	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	9900	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 16</u>	-	660	-	pF
C _{rss}	reverse transfer capacitance		-	381	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 0.67 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	45	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \ \Omega; \ I_D = 75 \ A; \ T_j = 25 \ ^{\circ}C$	-	91	-	ns
t _{d(off)}	turn-off delay time		-	122	-	ns
t _f	fall time		-	63	-	ns

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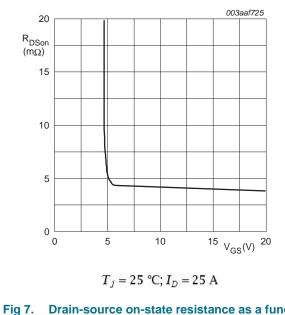
Characteristics continued					
Parameter	Conditions	Min	Тур	Max	Unit
rain diode					
source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; see <u>Figure 17</u>	-	0.8	1.2	V
reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	75	-	ns
recovered charge	$V_{GS} = 0 V; V_{DS} = 50 V$	-	235	-	nC
	Parameter rain diode source-drain voltage reverse recovery time	ParameterConditionsrain diodesource-drain voltage $I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C;$ see Figure 17reverse recovery time $I_S = 25 A; dI_S/dt = -100 A/\mu s;$ $V_{CS} = 0 V'; V_{CS} = 50 V/s$	ParameterConditionsMinrain diodesource-drain voltage $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 17-reverse recovery time $I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/µs};$ $V_{GS} = 0 \text{ V}; V_{GS} = 50 \text{ V}$	ParameterConditionsMinTyprain diodesource-drain voltage $I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C;$ see Figure 17-0.8reverse recovery time $I_S = 25 A; dI_S/dt = -100 A/\mus;$ $V_{GS} = 0 V'; V_{GS} = 50 V/s$ -75	ParameterConditionsMinTypMaxrain diodesource-drain voltage $I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C;$ see Figure 17-0.81.2reverse recovery time $I_S = 25 A; dI_S/dt = -100 A/\mus;$ $V_{GS} = 50 V/$ -75-

[1] Measured 3 mm from package.

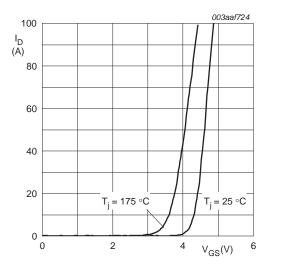


 $T_j = 25 \text{ °C}; V_{DS} = 25 \text{ V}$



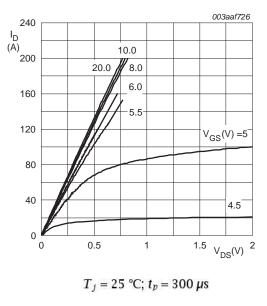












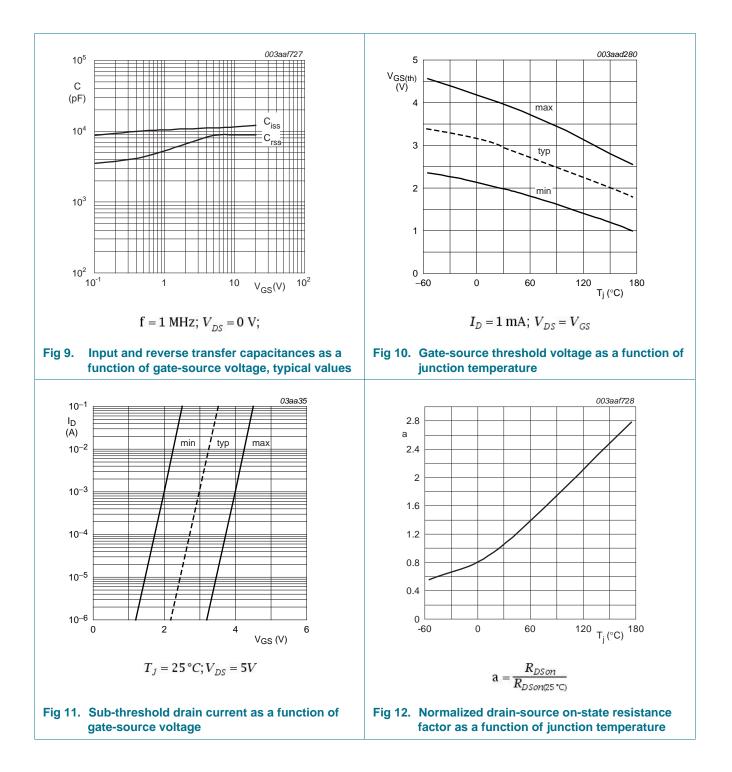


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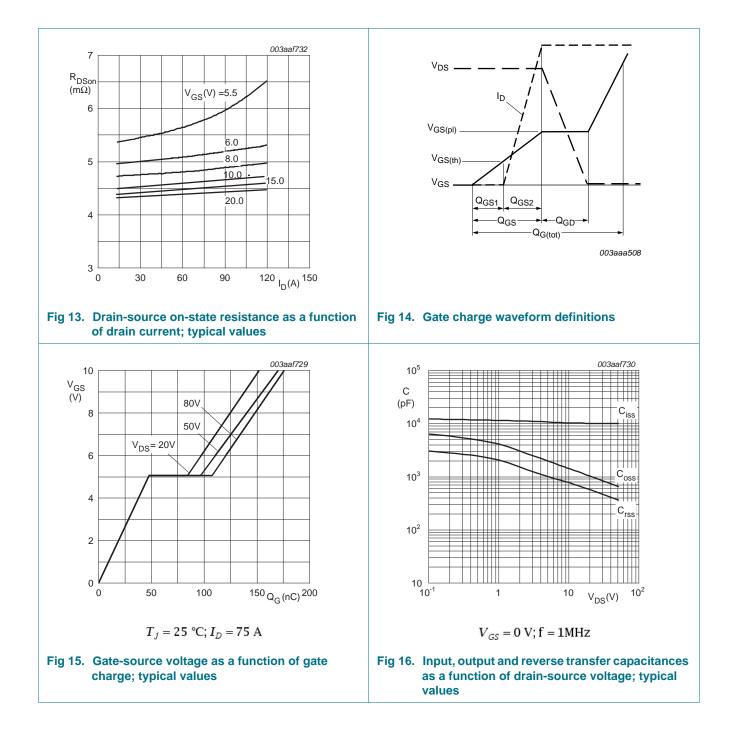
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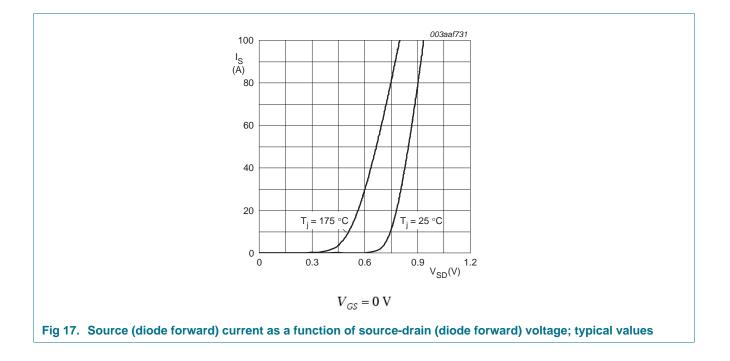
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7. Package outline

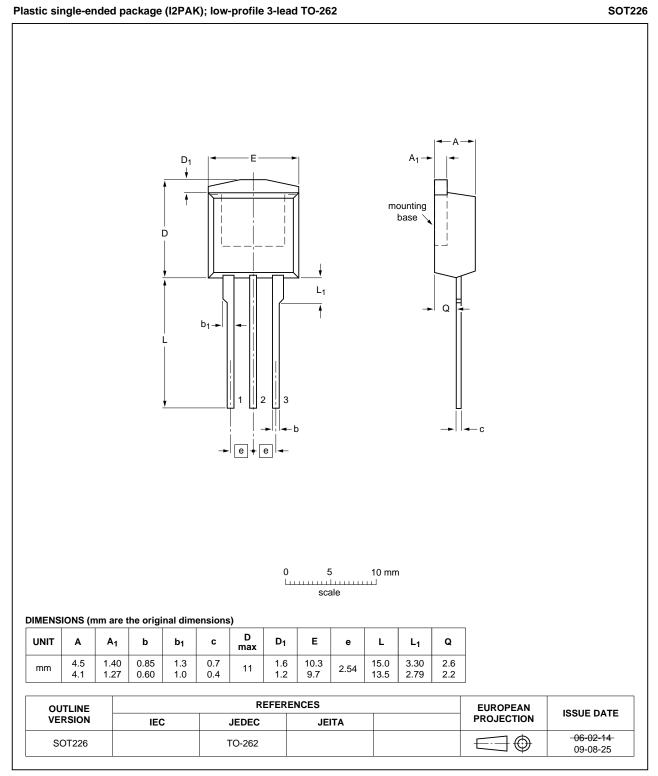


Fig 18. Package outline SOT226 (I2PAK)

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PSMN5R0-100ES

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8. Revision history

Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN5R0-100ES v.3	20110926	Product data sheet	-	PSMN5R0-100ES v.2
Modifications:	 Various changes to 	o content.		
PSMN5R0-100ES v.2	20110415	Product data sheet	-	PSMN5R0-100ES v.1

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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